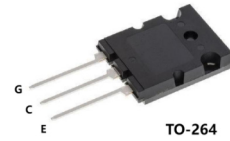


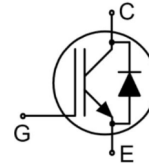
Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 10 μ s Short Circuit Capability



Applications

- Solar Inverter
- UPS



Absolute Ratings ($T_c=25^{\circ}C$)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	1200	V
Collector Current-continuous	I_C $T=25^{\circ}C$ $T=100^{\circ}C$	100	A
		50	A
Collector Current-pulse(note 1)	I_{CM}	200	A
Diode Continuous forward current	I_F $T=100^{\circ}C$	50	A
Diode Maximum Forward Current (Note 1)	I_{FM}	200	A
Gate-Emitter Voltage	V_{GES}	± 20	V
Short Circuit Withstand Time	tsc	10	us
Power Dissipation($T_c=25^{\circ}C$)	P_D $T_c=25^{\circ}C$ $T_c=100^{\circ}C$	535	W
Power Dissipation($T_c=100^{\circ}C$)		267	W
Operating Temperature Range	T_J	-55~+175	$^{\circ}C$
Storage Temperature Range	T_{STG}	-55~+175	$^{\circ}C$
Maximum Lead Temperature for Soldering Purposes	T_L	260	$^{\circ}C$

Electrical Characteristic ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Off-Characteristics						
Collector-Emitter Voltage	BV_{CES}	$I_C=500\mu A, V_{GE}=0V$	1200	-	-	V

MSG50T120FQW

Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$	-	-	0.1	mA
		$T_C=175^{\circ}C$			2.0	mA
Gate-body leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 200	nA
On-Characteristics						
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}, I_C=250\mu A$	4.5	5.5	6.5	V
Collector-Emitter saturation Voltage	V_{CESAT}	$V_{GE}=15V, I_C=50A, V_{GE}=15V, I_C=50A, T_J=175^{\circ}C$	-	2.20	2.40	V
				2.60		
Dynamic Characteristics						
Input capacitance	C_{ies}	$V_{CE}=20V, V_{GE}=0V, f=1.0MHz, T_C=25^{\circ}C$	-	7383	-	pF
Output capacitance	C_{oes}		-	233	-	pF
Reverse transfer capacitance	C_{res}		-	139	-	pF
Total Gate Charge	Q_g	$V_{CE}=600V, I_C=50A, V_{GE}=15V, T_C=25^{\circ}C$	-	311	-	nC
Gate to emitter charge	Q_{ge}		-	64	-	
Gate to collector charge	Q_{gc}		-	155	-	
Switching Characteristics						
Turn-On delay time	$t_d(on)$	$V_{CC}=600V, I_C=50A, R_G=10\Omega, V_{GE}=15V$ Inductive load $T_C=25^{\circ}C$	-	118	-	ns
Turn-On rise time	t_r		-	48	-	ns
Turn-off delay time	$t_d(off)$		-	282	-	ns
Turn-off Fall time	t_f		-	113	-	ns
Turn-on switching loss	E_{on}		-	4.40	-	mJ
Turn-off switching loss	E_{off}		-	1.40	-	mJ
Total switching loss	E_{ts}		-	5.80	-	mJ
Turn-On delay time	$t_d(on)$	$V_{CC}=600V, I_C=50A, R_G=10\Omega, V_{GE}=15V$ Inductive load $T_C=175^{\circ}C$	-	114	-	ns
Turn-On rise time	t_r		-	49	-	ns
Turn-off delay time	$t_d(off)$		-	298	-	ns
Turn-off Fall time	t_f		-	243	-	ns
Turn-on switching loss	E_{on}		-	5.65	-	mJ
Turn-off switching loss	E_{off}		-	3.26	-	mJ
Total switching loss	E_{ts}		-	8.91	-	mJ
Anti-Parallel Diode Characteristics and Maximum Ratings						
Diode Forward Voltage	V_F	$V_{GE}=0V, I_F=50A.$	-	2.00	2.60	V
		$T_J=175^{\circ}C$		2.55		

MSG50T120FQW

Diode Reverse recovery time	t_{rr}	$V_R=400V, I_F=50A$ $di_F/dt=200A/us$ $T_J=25^\circ C$	-	256	-	ns
Reverse recovery charge	Q_{rr}		-	2.7	-	μC
Diode Reverse recovery Current	I_{rrm}		-	19	-	A
Diode Reverse recovery time	t_{rr}	$V_R=400V, I_F=50A$ $di_F/dt=200A/us$ $T_J=175^\circ C$	-	400	-	ns
Reverse recovery charge	Q_{rr}		-	5.75	-	μC
Diode Reverse recovery Current	I_{rrm}		-	27	-	A

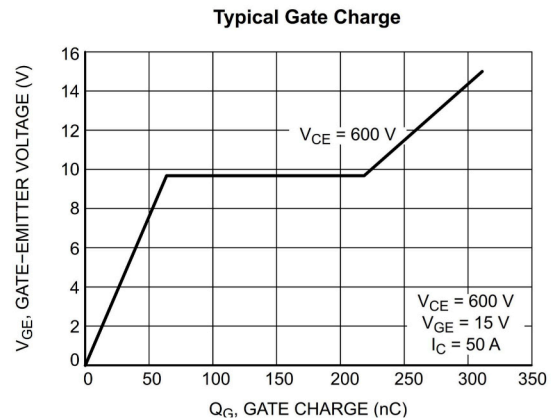
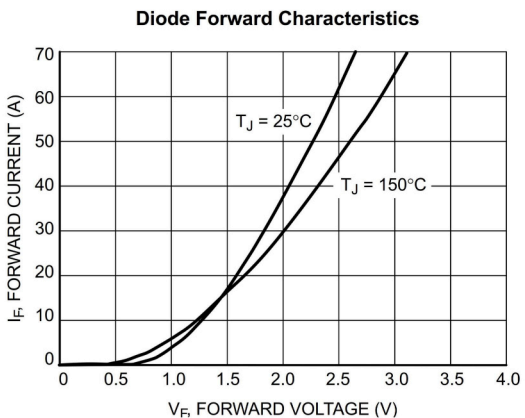
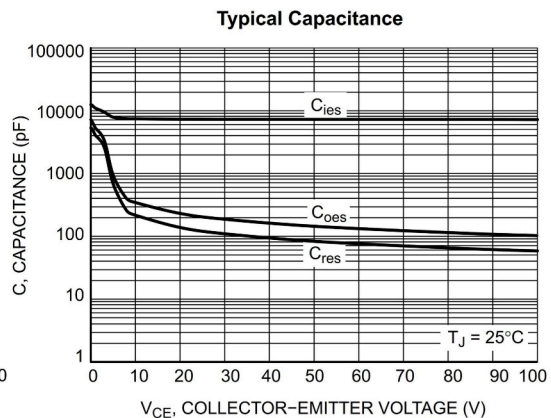
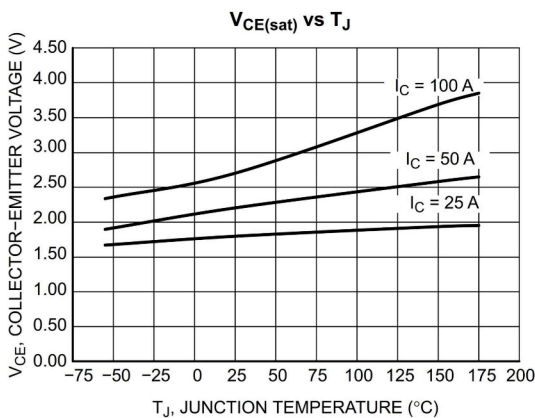
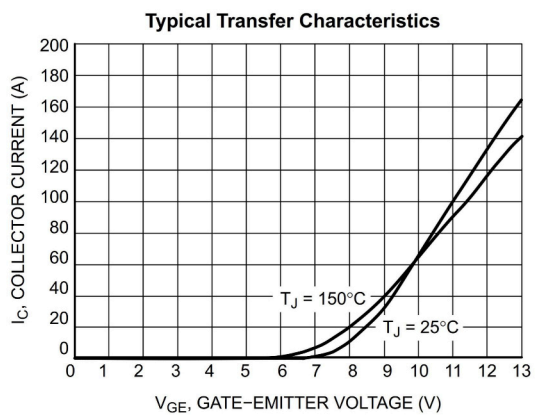
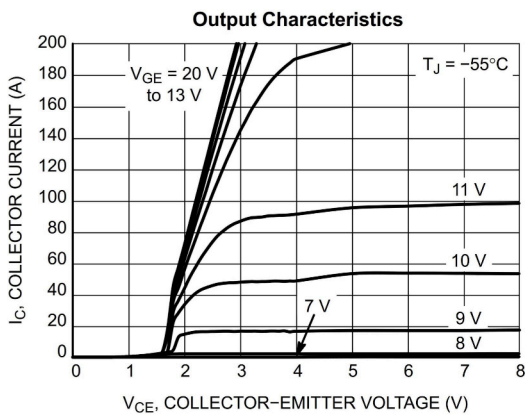
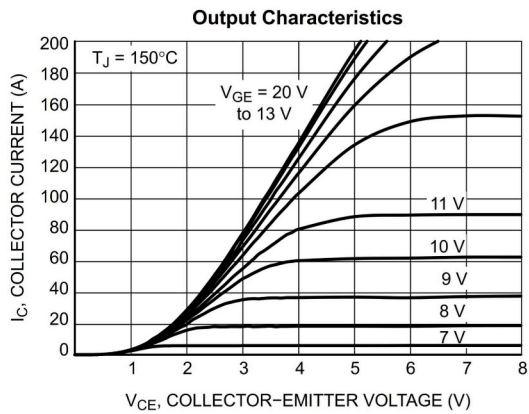
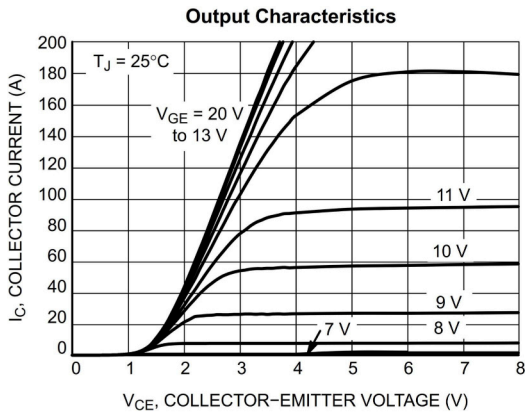
Thermal Characteristics

Symbol	Parameter	Max	Units
$R_{th\ j-c}$	Thermal Resistance, Junction to case for IGBT	0.28	$^\circ C/W$
$R_{th\ j-c}$	Thermal Resistance, Junction to case for Diode	0.5	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$

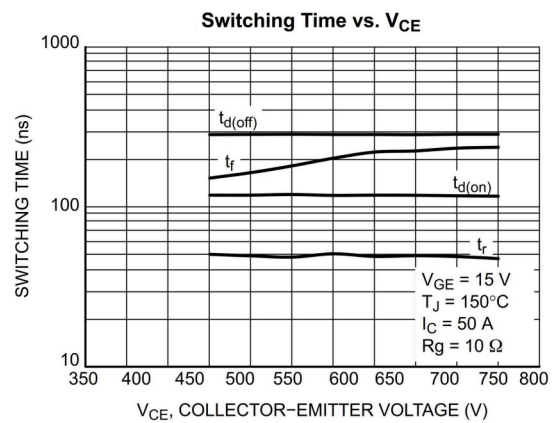
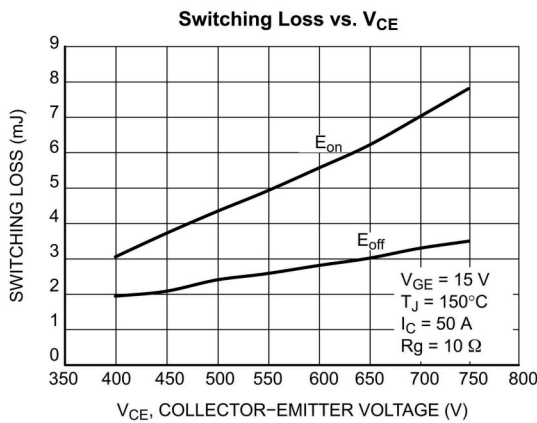
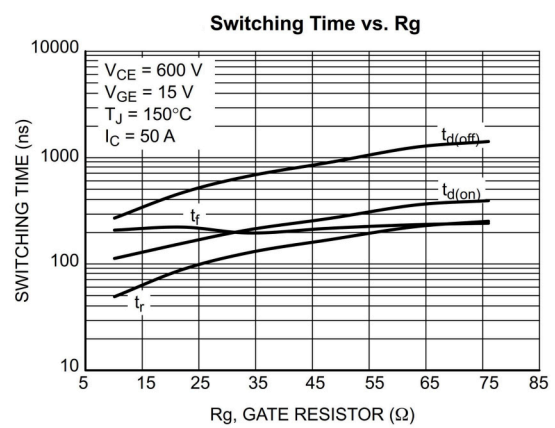
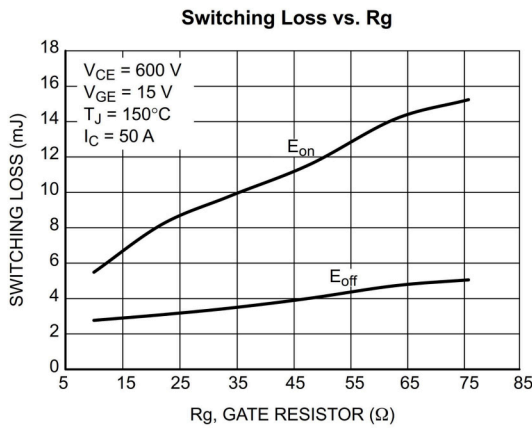
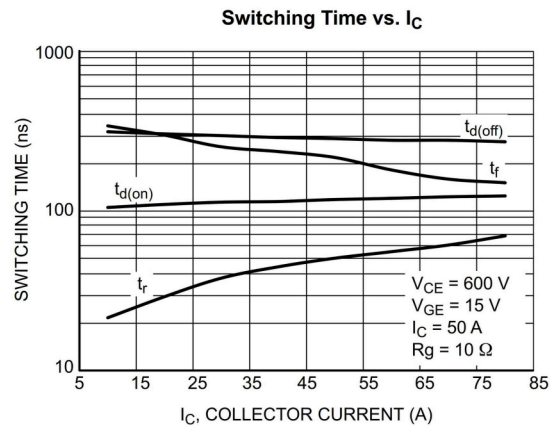
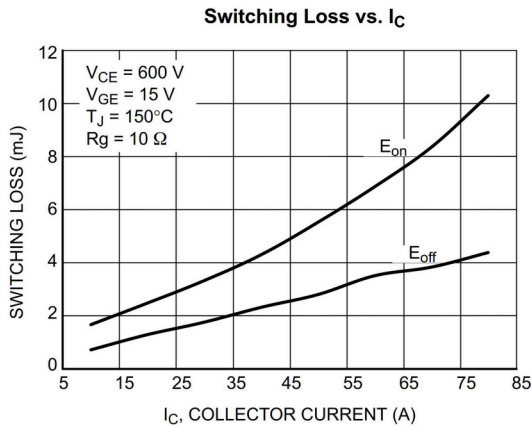
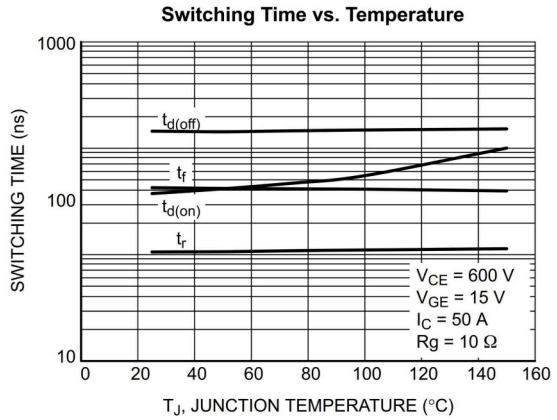
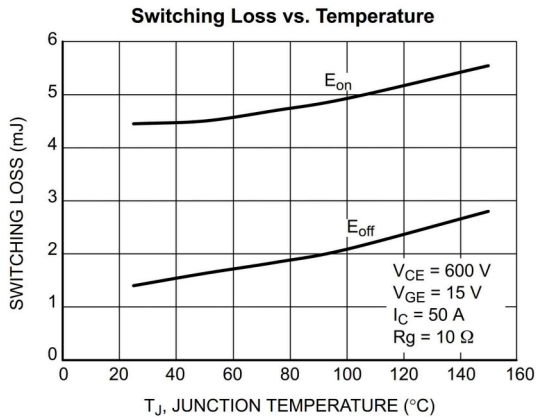
Notes:

1: . Repetitive Rating: Pulse width limited by maximum junction temperature

Electrical Characteristics (curves)

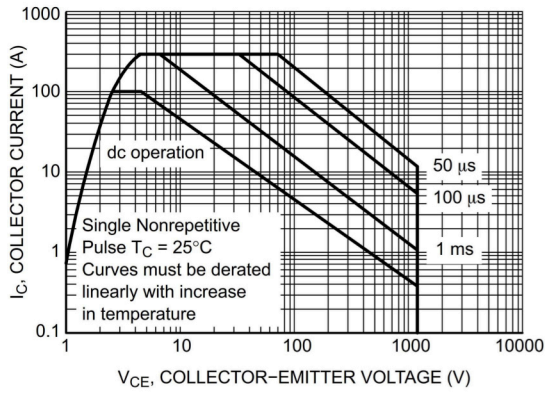


MSG50T120FQW

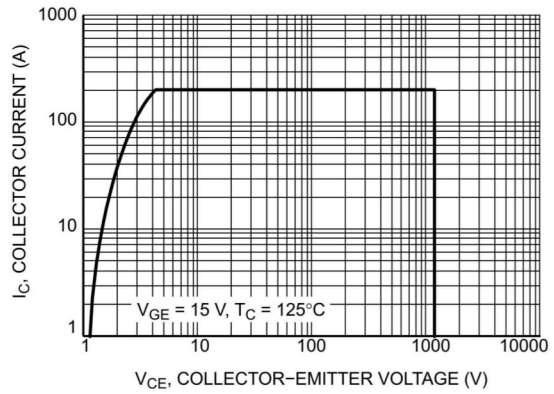


MSG50T120FQW

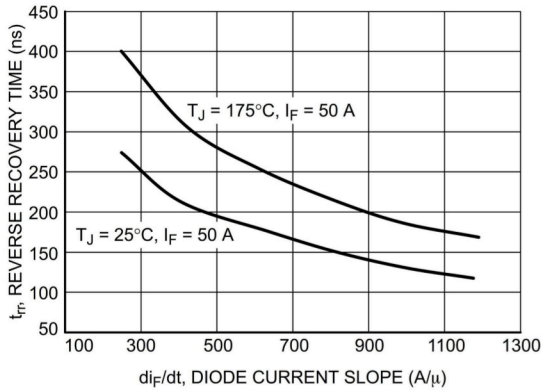
Safe Operating Area



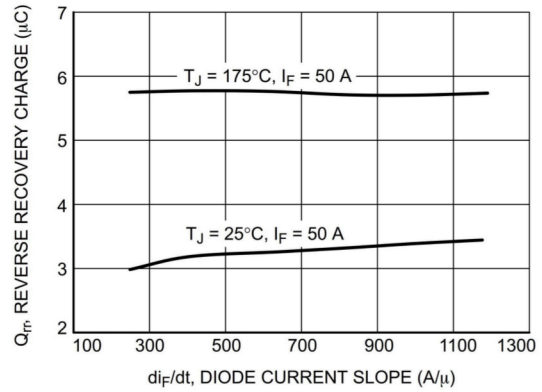
Reverse Bias Safe Operating Area



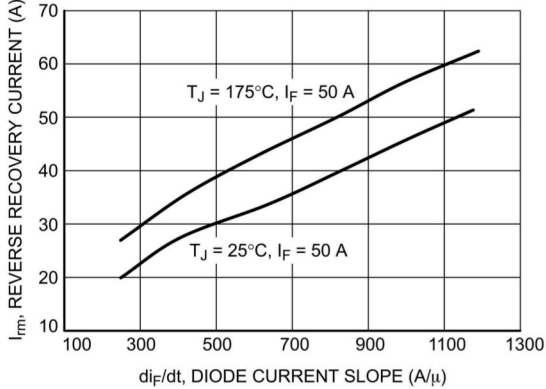
t_{rr} vs. di_F/dt (V_R = 400 V)



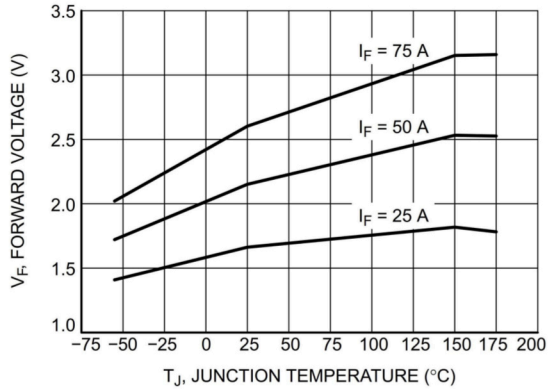
Q_{rr} vs. di_F/dt (V_R = 400 V)



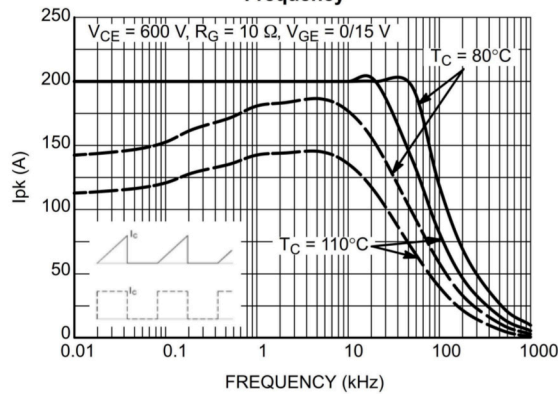
I_{rm} vs. di_F/dt (V_R = 400 V)



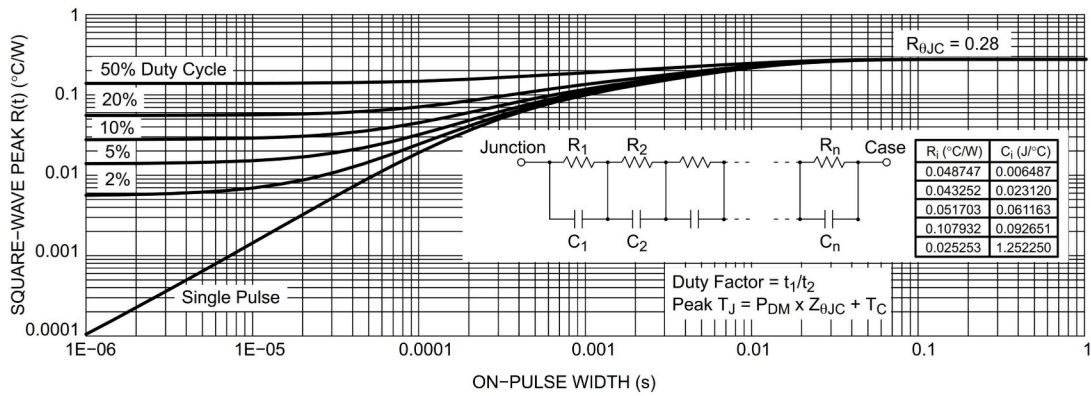
V_F vs. T_J



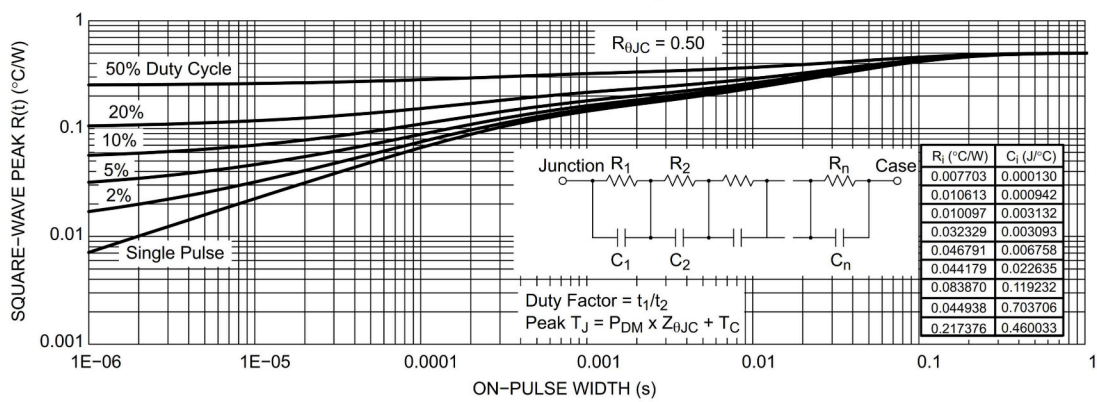
Collector Current vs. Switching Frequency



IGBT Transient Thermal Impedance



Diode Transient Thermal Impedance



Package Mechanical DATA

